Important notice

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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

PDTB1xxxT series

500 mA, 50 V PNP resistor-equipped transistors

Rev. 1 — 13 May 2014 Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package			NPN complement	Package configuration
	NXP	JEITA	JEDEC		
PDTB143ET	SOT23	TO-236AB	-	PDTD143ET	small
PDTB143XT				PDTD143XT	
PDTB114ET				PDTD114ET	

1.2 Features

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- ± 10 % resistor ratio tolerance
- AEC-Q101 qualified
- High temperature applications up to 175 °C

1.3 Applications

- IC inputs control
- Cost-saving alternative to BC807 or BC817 series transistors in digital applications
- Switching loads

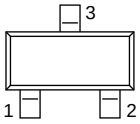
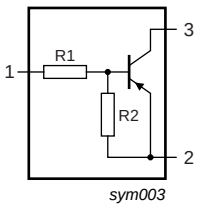
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	–50	V
I_O	output current		-	-	–500	mA
R1	bias resistor 1 (input)					
	PDTB143ET			4.7		kΩ
	PDTB143XT			4.7		kΩ
	PDTB114ET			10		kΩ
R2	bias resistor 2 (base-emitter)					
	PDTB143ET			4.7		kΩ
	PDTB143XT			10		kΩ
	PDTB114ET			10		kΩ

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	input (base)		
2	GND (emitter)		
3	output (collector)		

sym003

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTB1xxxT series	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTB143ET	*4X
PDTB143XT	*4Y
PDTB114ET	*09

[1] * = placeholder for manufacturing site code

5. Limiting values

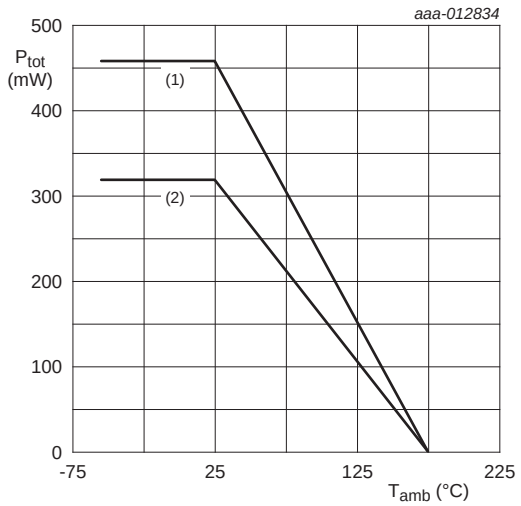
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	–50	V
V_{CEO}	collector-emitter voltage	open base	-	–50	V
V_{EBO}	emitter-base voltage	open collector			
	PDTB143ET		-	–10	V
	PDTB143XT		-	–7	V
	PDTB114ET		-	–10	V
V_I	input voltage				
	PDTB143ET		–30	+10	V
	PDTB143XT		–30	+7	V
	PDTB114ET		–50	+10	V
I_O	output current		-	–500	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C [1]	-	320	mW
		[2]	-	460	mW
T_j	junction temperature		-	175	°C
T_{amb}	ambient temperature		–55	+175	°C
T_{stg}	storage temperature		–55	+175	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



(1) FR4 PCB, 4-layer copper, standard footprint

(2) FR4 PCB, single-sided copper, standard footprint.

Fig 1. Power derating curves

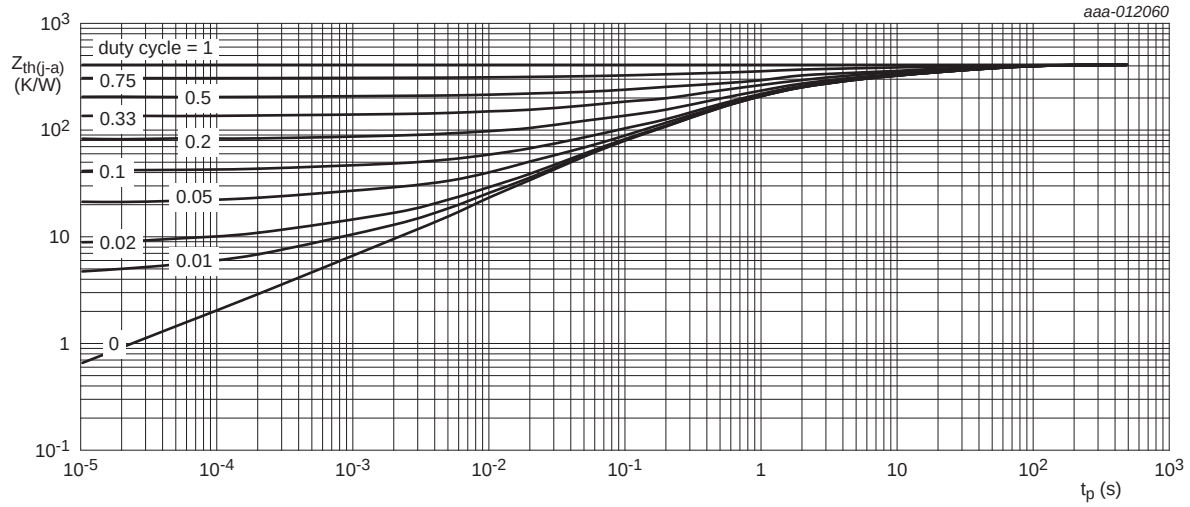
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	470	K/W
			[2]	-	-	327	K/W

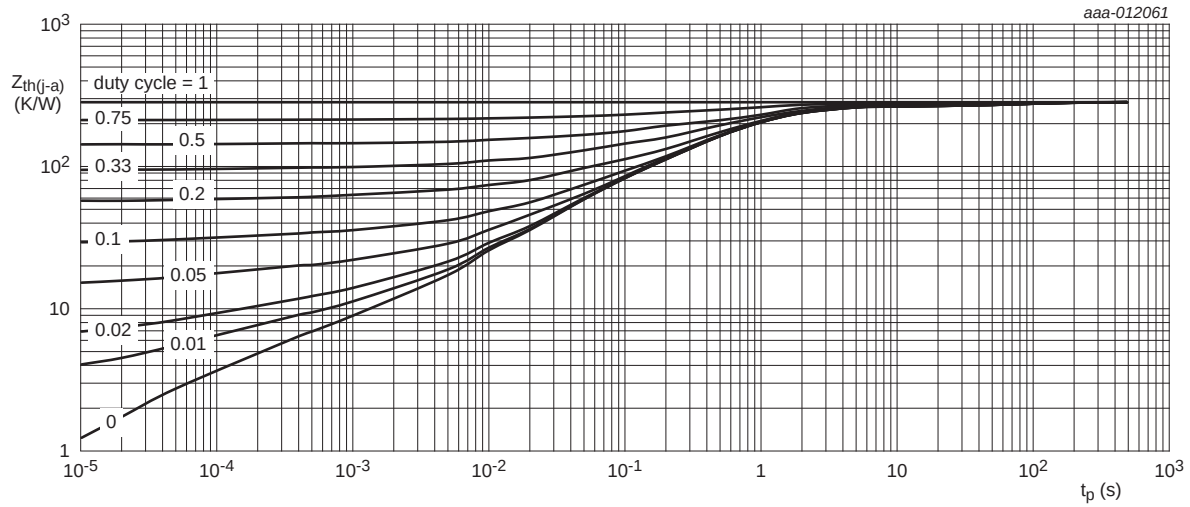
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23/TO-236AB; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23/TO-236AB; typical values

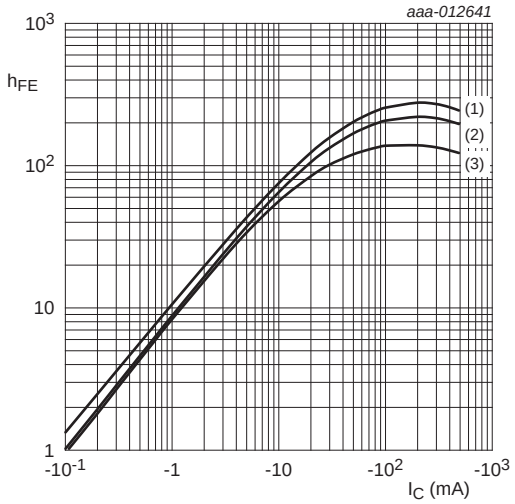
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = –40 V; I_E = 0 A	-	-	–100	nA
		V_{CB} = –50 V; I_E = 0 A	-	-	–100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = –50 V; I_B = 0 A	-	-	–0.5	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0 A				
	PDTB143ET		-	-	–0.9	mA
	PDTB143XT		-	-	–0.6	mA
	PDTB114ET		-	-	–0.4	mA
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –50 mA				
	PDTB143ET		60	-	-	
	PDTB143XT		70	-	-	
	PDTB114ET		70	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = –50 mA; I_B = –2.5 mA	-	-	–100	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = –5 V; I_C = –100 μA				
	PDTB143ET		–0.6	–0.9	–1.5	V
	PDTB143XT		–0.5	–0.75	–1.1	V
	PDTB114ET		–0.6	–1.0	–1.5	V
$V_{I(on)}$	on-state input voltage	V_{CE} = –0.3 V; I_C = –20 mA				
	PDTB143ET		–1.0	–1.7	–2.2	V
	PDTB143XT		–1.0	–1.4	–2.0	V
	PDTB114ET		–1.0	–2.2	–3.0	V
R1	bias resistor 1 (input)					
	PDTB143ET		3.3	4.7	6.1	kΩ
	PDTB143XT		3.3	4.7	6.1	kΩ
	PDTB114ET		7.0	10	13	kΩ
R2/R1	bias resistor ratio					
	PDTB143ET		0.9	1.0	1.1	
	PDTB143XT		1.91	2.13	2.34	
	PDTB114ET		0.9	1.0	1.1	
C_c	collector capacitance	V_{CB} = –10 V; $I_E = i_e$ = 0 A; f = 1 MHz	-	11	-	pF
f_T	transition frequency	V_{CE} = –5 V; I_C = –50 mA; f = 100 MHz [1]	-	140	-	MHz

[1] Characteristics of built-in transistor.



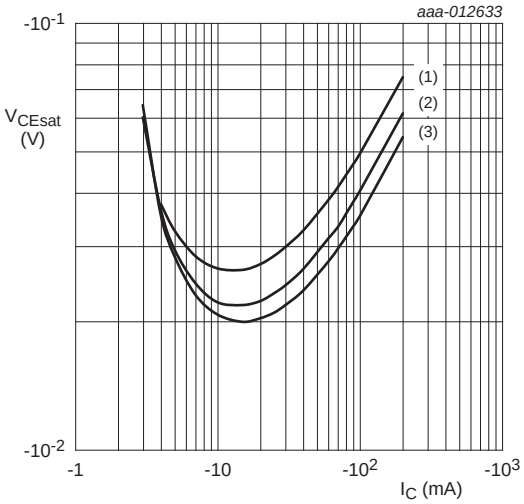
V_{CE} = –5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = –40 °C

Fig 4. PDTB143ET: DC current gain as a function of collector current; typical values



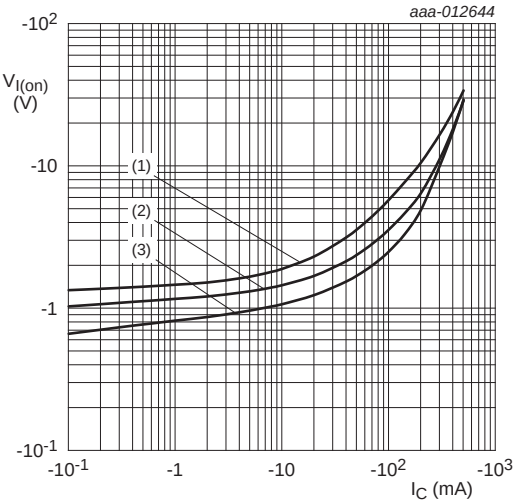
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = –40 °C

Fig 5. PDTB143ET: Collector-emitter saturation voltage as a function of collector current; typical values



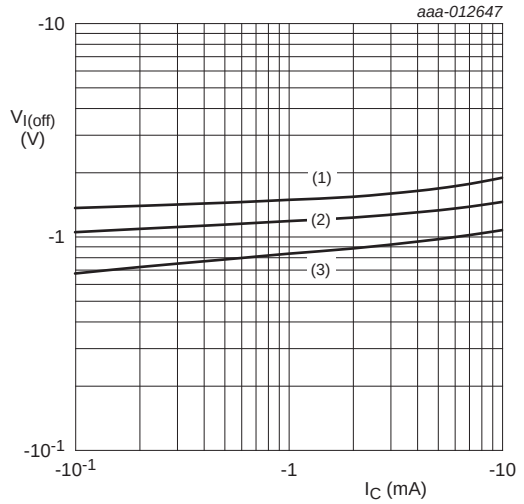
V_{CE} = –0.3 V

(1) T_{amb} = –40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 6. PDTB143ET: On-state input voltage as a function of collector current; typical values



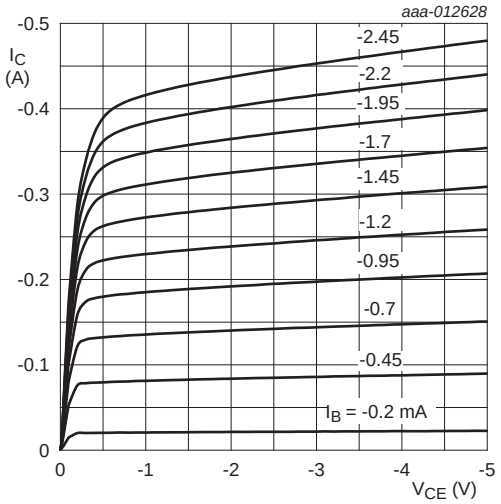
V_{CE} = –5 V

(1) T_{amb} = –40 °C

(2) T_{amb} = 25 °C

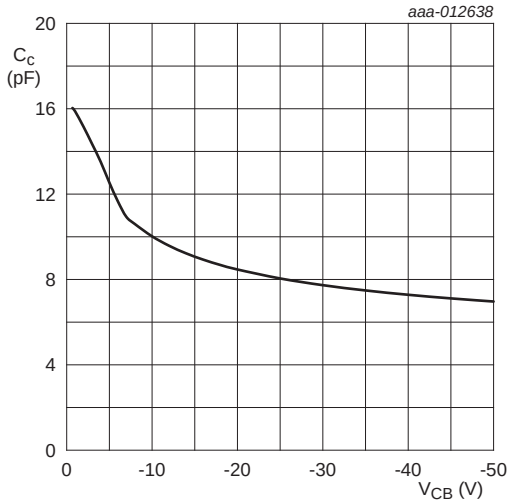
(3) T_{amb} = 100 °C

Fig 7. PDTB143ET: Off-state input voltage as a function of collector current; typical values



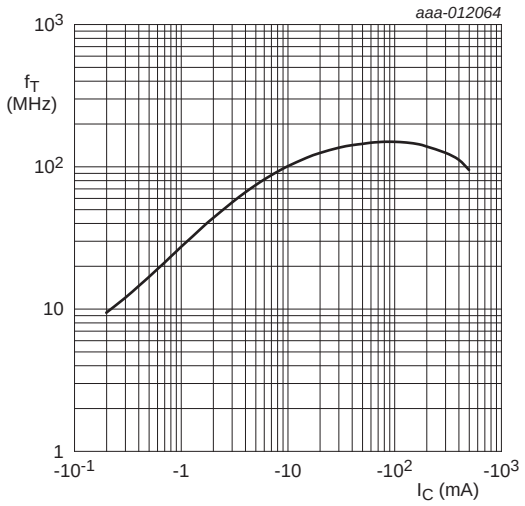
T_{amb} = 25 °C

Fig 8. PDTB143ET: Collector current as a function of collector-emitter voltage; typical values



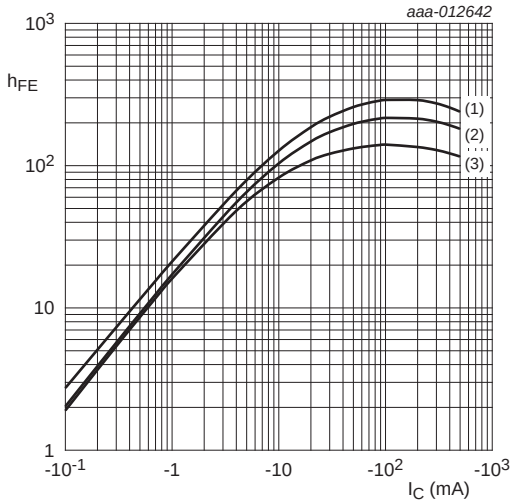
f = 1 MHz; T_{amb} = 25 °C

Fig 9. PDTB143ET: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = −5 V; T_{amb} = 25 °C

Fig 10. PDTB143ET: Transition frequency as a function of collector current; typical values of built-in transistor



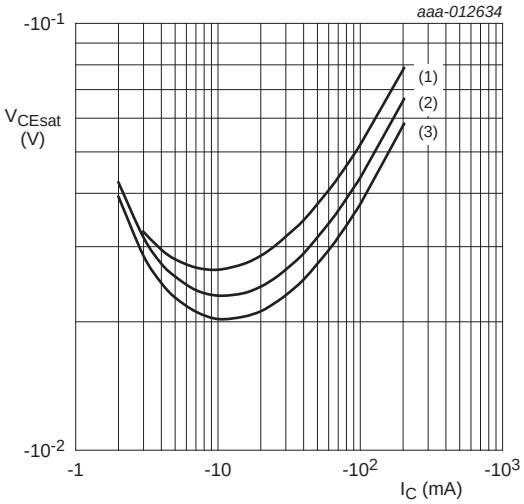
V_{CE} = –5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = –40 °C

Fig 11. PDTB143XT: DC current gain as a function of collector current; typical values



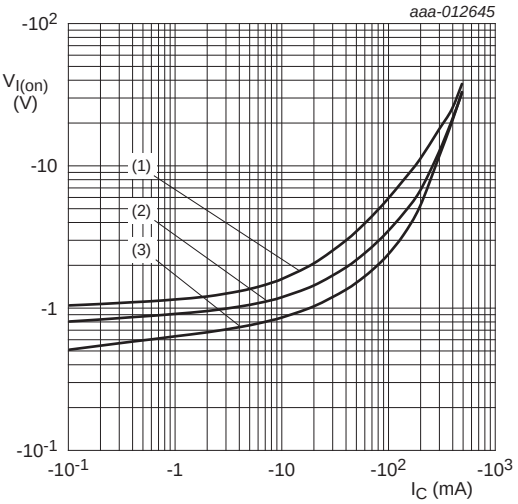
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = –40 °C

Fig 12. PDTB143XT: Collector-emitter saturation voltage as a function of collector current; typical values



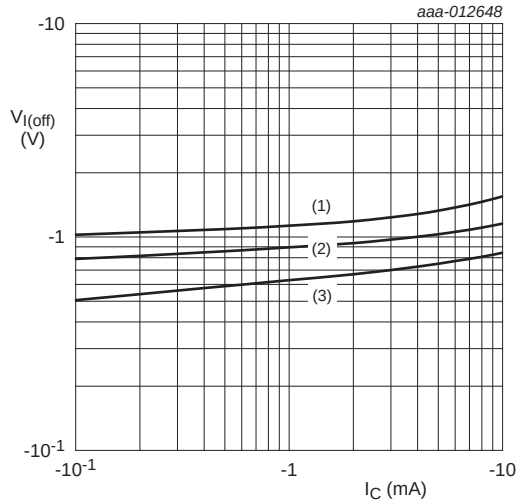
V_{CE} = –0.3 V

(1) T_{amb} = –40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 13. PDTB143XT: On-state input voltage as a function of collector current; typical values



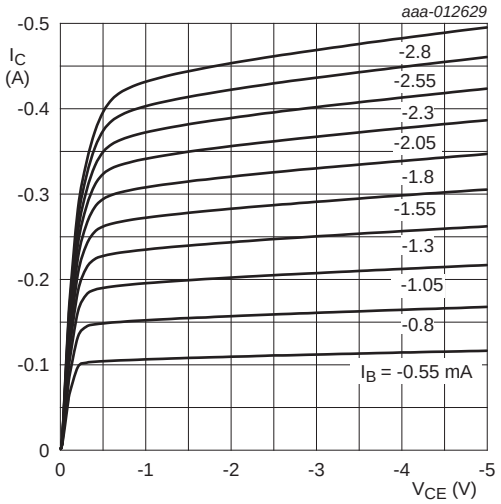
V_{CE} = –5 V

(1) T_{amb} = –40 °C

(2) T_{amb} = 25 °C

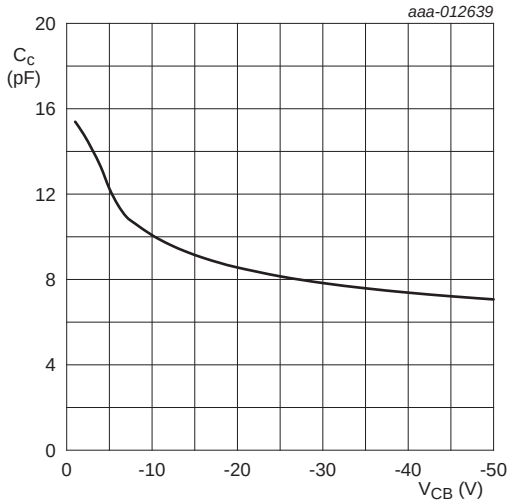
(3) T_{amb} = 100 °C

Fig 14. PDTB143XT: Off-state input voltage as a function of collector current; typical values



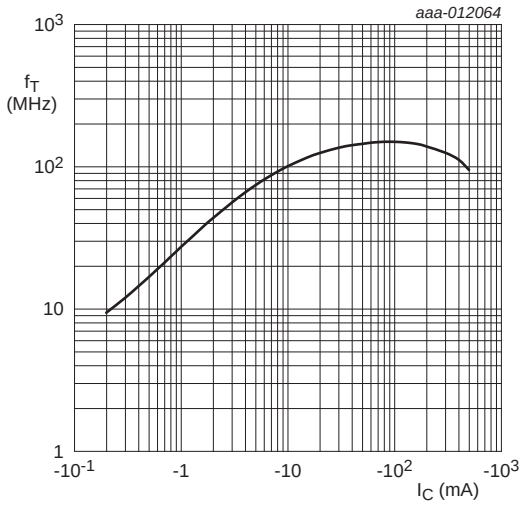
T_{amb} = 25 °C

Fig 15. PDTB143XT: Collector current as a function of collector-emitter voltage; typical values



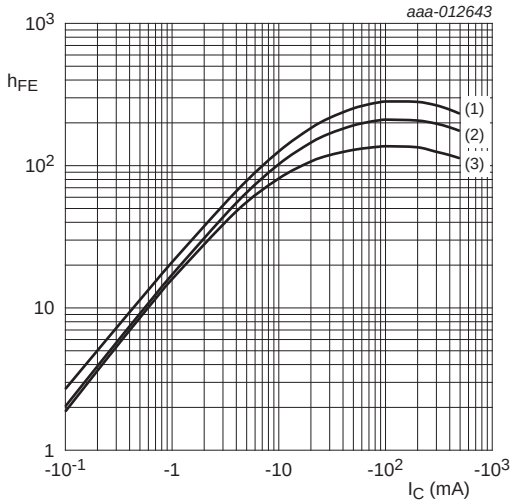
f = 1 MHz; T_{amb} = 25 °C

Fig 16. PDTB143XT: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = −5 V; T_{amb} = 25 °C

Fig 17. PDTB143XT: Transition frequency as a function of collector current; typical values of built-in transistor



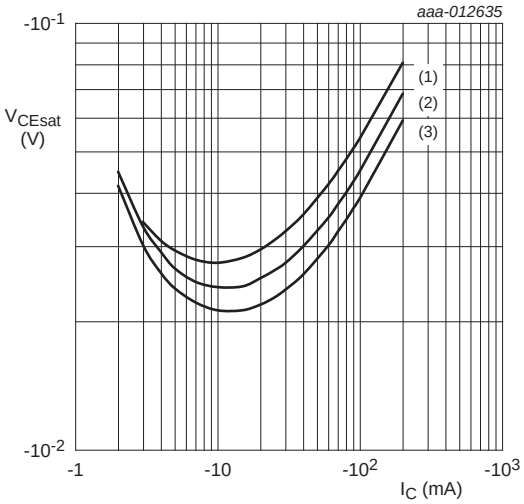
V_{CE} = −5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 18. PDTB114ET: DC current gain as a function of collector current; typical values



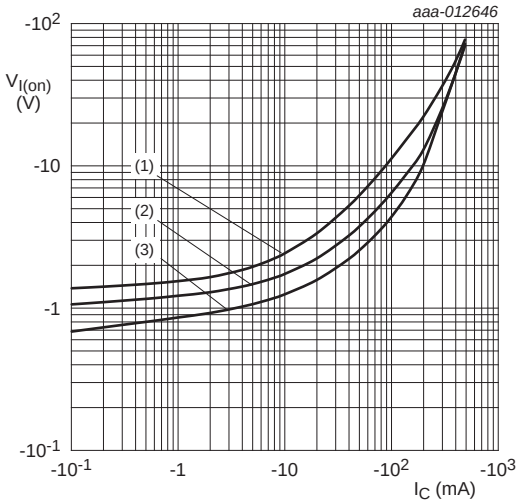
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 19. PDTB114ET: Collector-emitter saturation voltage as a function of collector current; typical values



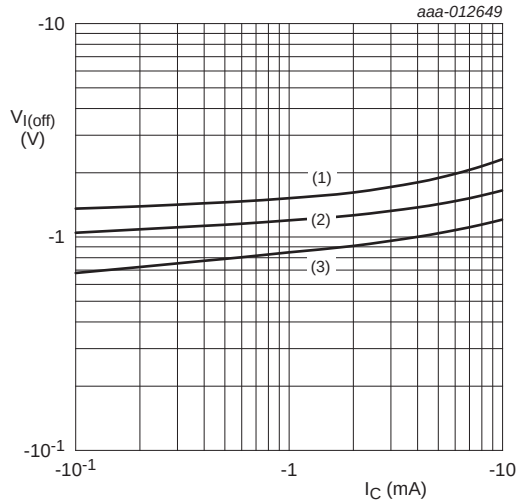
V_{CE} = −0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 20. PDTB114ET: On-state input voltage as a function of collector current; typical values



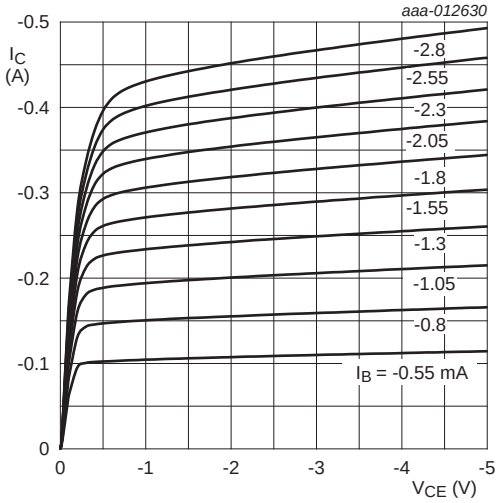
V_{CE} = −5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

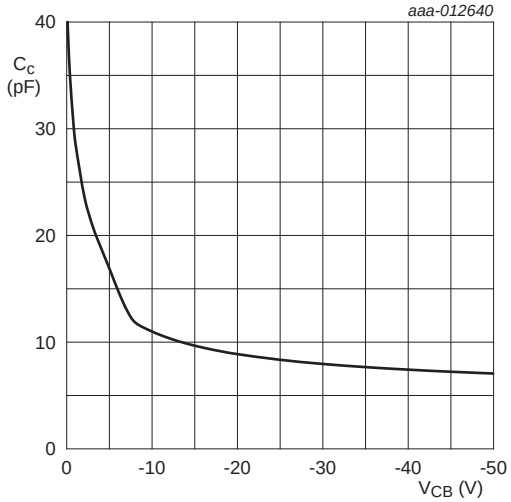
(3) T_{amb} = 100 °C

Fig 21. PDTB114ET: Off-state input voltage as a function of collector current; typical values



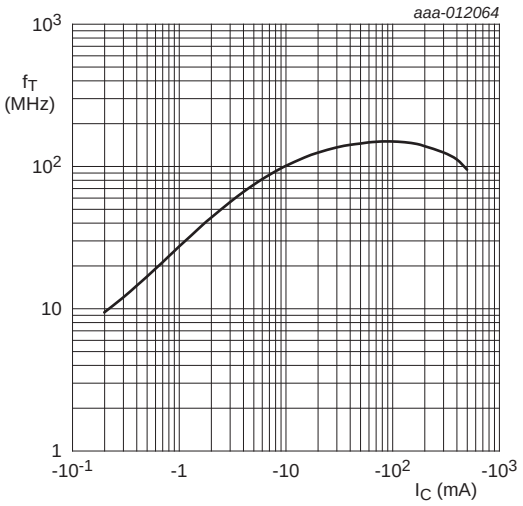
T_{amb} = 25 °C

Fig 22. PDTB114ET: Collector current as a function of collector-emitter voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 23. PDTB114ET: Collector capacitance as a function of collector-base voltage; typical values of built-in transistor



V_{CE} = −5 V; T_{amb} = 25 °C

Fig 24. PDTB114ET: Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

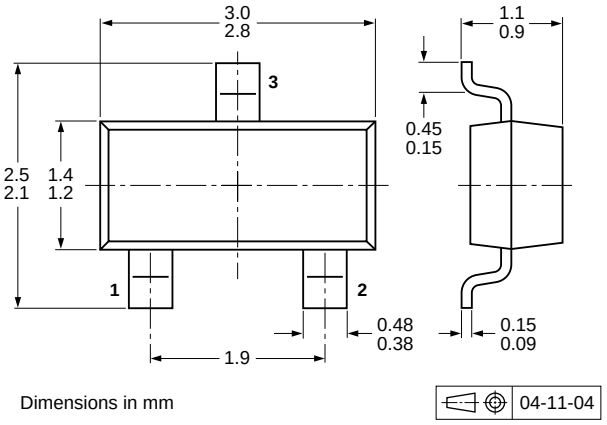
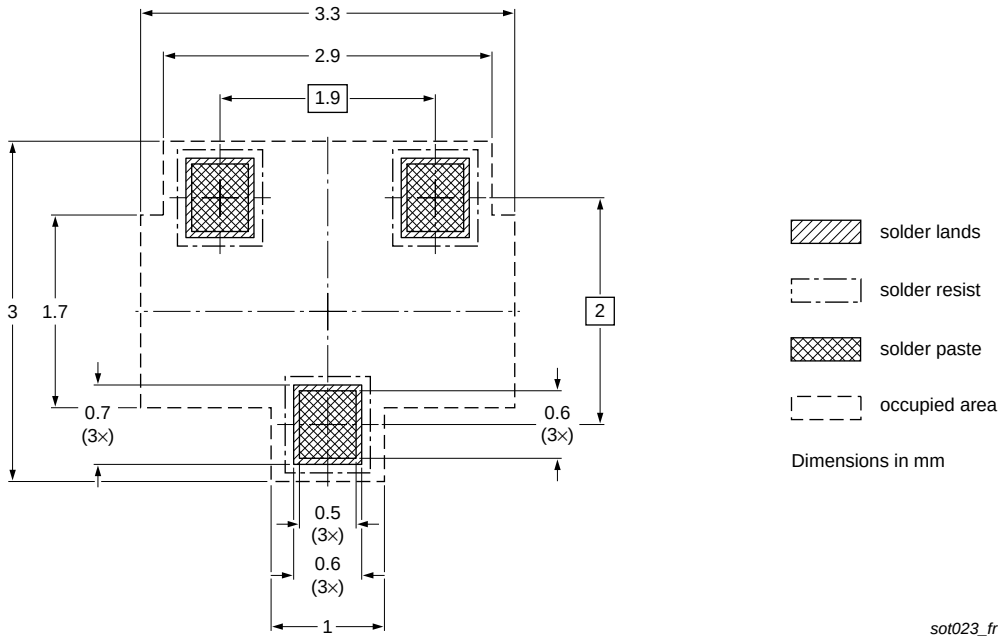


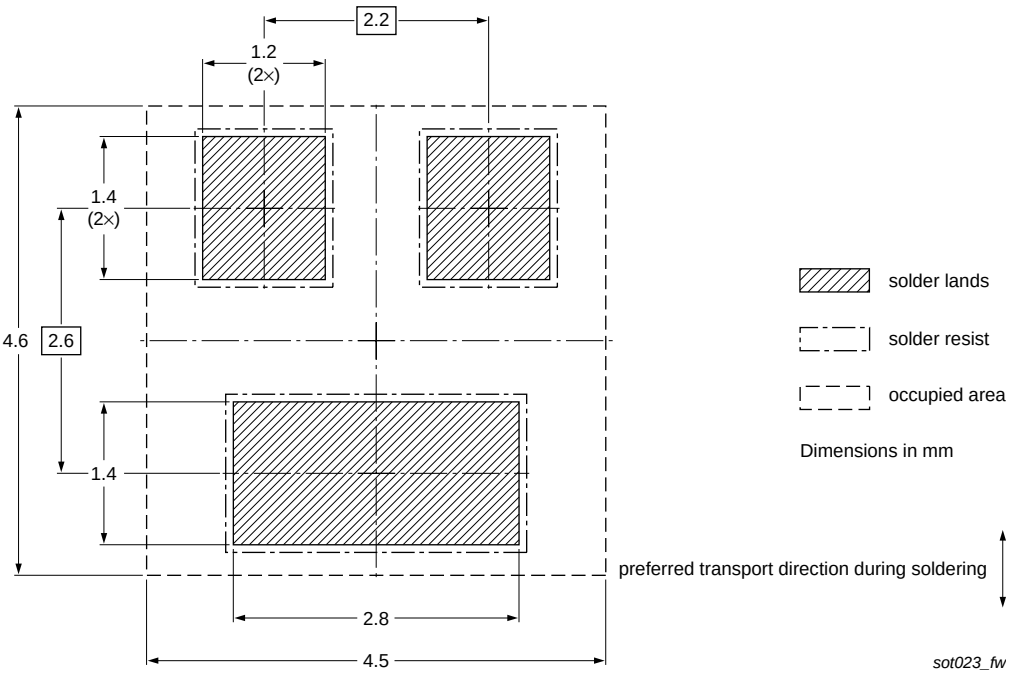
Fig 25. Package outline PDTB1xxxT series (SOT23/TO-236AB)

10. Soldering



Dimensions in mm

Fig 26. Reflow soldering footprint PDTB1xxxT series (SOT23/TO-236AB)



Dimensions in mm

Fig 27. Wave soldering footprint PDTB1xxxT series (SOT23/TO-236AB)

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB1XXXT_SER v.1	20140513	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

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13. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

14. Contents

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